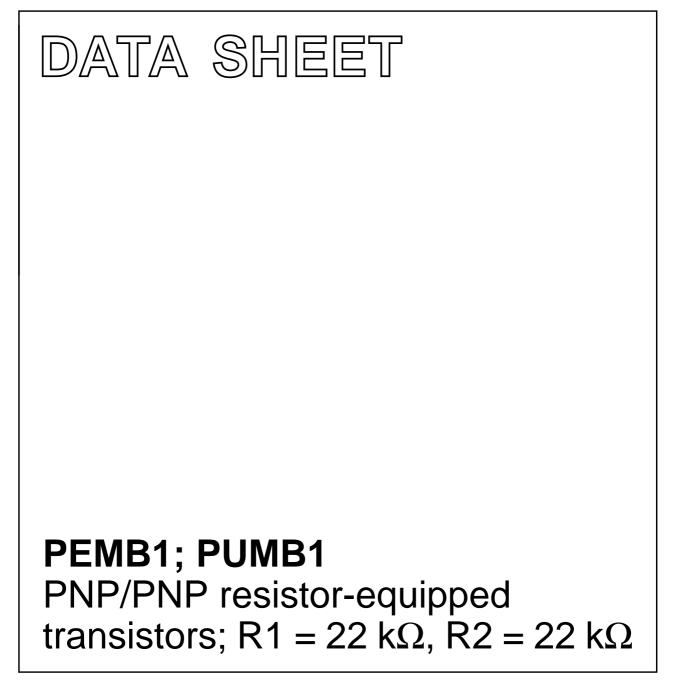
DISCRETE SEMICONDUCTORS



Product specification Supersedes data of 2001 Sep 13 2003 Oct 15



PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 22 k Ω

PEMB1; PUMB1

FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- Low current peripheral drivers
- Replacement of general purpose transistors in digital applications.

DESCRIPTION

PNP/PNP resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	-	-50	V
l _o	output current (DC)	_	-100	mA
TR1	PNP	-	_	-
TR2	PNP	-	-	-
R1	bias resistor	22	_	kΩ
R2	bias resistor	22	-	kΩ

	PAC	PACKAGE		NPN/PNP	NPN/NPN	
ITFE NUMBER	PHILIPS	EIAJ	MARKING CODE	COMPLEMENT	COMPLEMENT	
PEMB1	SOT666	-	Z4	PEMD2	PEMH1	
PUMB1	SOT363	SC-88	B*3 ⁽¹⁾	PUMD2	PUMH1	

Note

- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	MBER SIMPLIFIED OUTLINE AND SYMBOL		PINNING		
	SIMPLIFIED OUTLINE AND STMBOL	PIN	DESCRIPTION		
PEMB1	6 5 4	1	emitter TR1		
PUMB1		2	base TR1		
		3	collector TR2		
		4	emitter TR2		
		5	base TR2		
		6	collector TR1		
	Top view MAM477				

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PEMB1; PUMB1

ORDERING INFORMATION

TYPE NUMBER		PACKAGE		
NAME		DESCRIPTION	VERSION	
PEMB1	 plastic surface mounted package; 6 leads 		SOT666	
PUMB1	 plastic surface mounted package; 6 leads SO 		SOT363	

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	PARAMETER CONDITIONS		MAX.	UNIT	
Per transi	stor	ł	L. L			
V _{CBO}	collector-base voltage	open emitter	_	-50	V	
V _{CEO}	collector-emitter voltage	open base	-	-50	V	
V _{EBO}	emitter-base voltage	open collector	-	-10	V	
VI	input voltage positive negative		-	+10 -40	V V	
I _O	output current (DC)		_	-100	mA	
I _{CM}	peak collector current		_	-100	mA	
P _{tot}	total power dissipation SOT363 SOT666	$T_{amb} \le 25 \ ^{\circ}C$ note 1 notes 1 and 2	-	200 200	mW mW	
T _{stg}	storage temperature		-65	+150	°C	
Tj	junction temperature		_	150	°C	
T _{amb}	operating ambient temperature		-65	+150	°C	
Per device	•					
P _{tot}	total power dissipation SOT363 SOT666	$T_{amb} \le 25 \text{ °C}$ note 1 notes 1 and 2	-	300 300	mW mW	

Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.

2. Reflow soldering is the only recommended soldering method.

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PEMB1; PUMB1

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or	•		
R _{th j-a}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device	•	· ·		
R _{th j-a}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	note 1	416	K/W

Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.

2. Reflow soldering is the only recommended soldering method.

CHARACTERISTICS

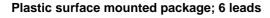
 T_{amb} = 25 °C unless otherwise specified.

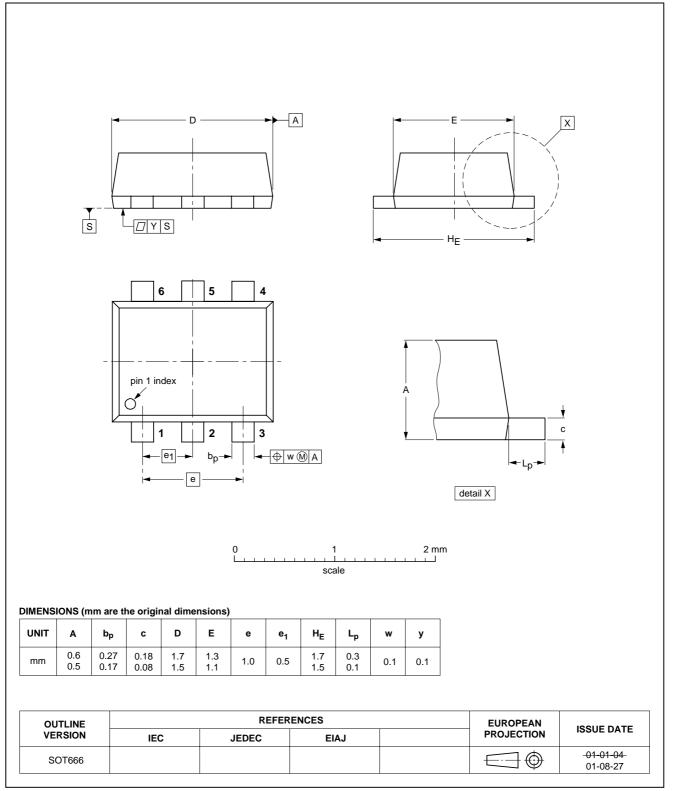
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; \text{ I}_{E} = 0$	-	-	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0$	-	-	-1	μA
		$V_{CE} = -30 \text{ V}; I_B = 0; T_j = 150 \text{ °C}$	-	-	-50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0$	-	-	-180	μA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	60	-	-	
V _{CEsat}	saturation voltage	$I_{\rm C} = -10 \text{ mA}; I_{\rm B} = -0.5 \text{ mA}$	-	-	-150	mV
V _{i(off)}	input-off voltage	$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -100 \mu\text{A}$	-	-1.1	-0.8	V
V _{i(on)}	input-on voltage	$V_{CE} = -0.3 \text{ V}; I_C = -5 \text{ mA}$	-2.5	-1.7	-	V
R1	input resistor		15.4	22	28.6	kΩ
R2 R1	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$I_E = i_e = 0; V_{CB} = -10 V;$ f = 1 MHz	-	-	3	pF

PEMB1; PUMB1

PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 22 k Ω

PACKAGE OUTLINES





SOT666

PNP/PNP resistor-equipped transistors; $R1 = 22 \text{ k}\Omega$, $R2 = 22 \text{ k}\Omega$

PEMB1; PUMB1

Plastic surface mounted package; 6 leads Х В А □ у Η_E = v M A 5 Q pin 1 index A₁ 3 1 2 t С 1 • 🕂 w 🕅 B e₁ bp' Lp е detail X 0 1 2 mm scale DIMENSIONS (mm are the original dimensions) A1 Η_E UNIT D Е Q Α bp с е e₁ Lp v w у max 0.30 2.2 1.8 1.35 1.15 0.25 0.45 0.25 2.2 2.0 1.1 0.1 1.3 0.65 0.2 0.2 0.1 mm 0.8 0.20 0.10 0.15 0.15 REFERENCES OUTLINE VERSION EUROPEAN **ISSUE DATE** PROJECTION IEC JEDEC EIAJ $\square \bigcirc$ SOT363 SC-88 97-02-28

PNP/PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 22 k Ω

PEMB1; PUMB1

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
11	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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